

64 K × 4 High Speed CMOS SRAM

Short description. Please refer to the full datasheet available on TEMIC web for detailed technical information.

Description

The HM 65798 is a high speed CMOS static RAM organized as $65,536 \times 4$ bit. It is manufactured using TEMIC high performance CMOS technology.

Access times as fast 20 ns are available with maximum power consumption of only 770 mW.

The HM 65798 features fully static operation requiring no external clocks or timing strobes. The automatic power-down feature reduces the power consumption by 71 % when the circuit is deselected.

Easy memory expansion is provided by an active low chip select (\overline{CS}) and three state drivers.

All inputs and outputs of the HM 65798 are TTL compatible and operate from single 5 V supply thus simplifying system design.

The HM 65798 is 100 % processed following the test methods of MIL STD 883 making ideally suitable for military applications that demand superior levels of performance and reliability.

Features

Fast access time

Commercial/industrial: 20/25/35/45/55 ns (max)

Military: 25/35/45/55 ns (max)

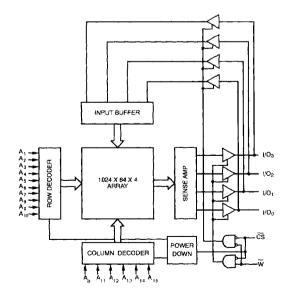
• Low power consumption

Active: 770 mW Standby: 220 mW

- Wide temperature range: -55°C to + 125°C
- 300 mils width package
- TTL compatible inputs and outputs
- Asynchronous
- Capable of withstanding greater than 2000V electrostatic discharge single 5 volt supply

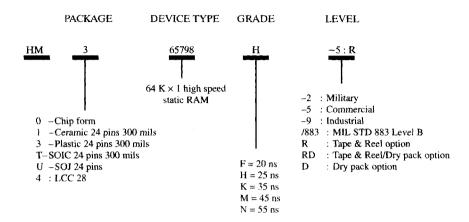
Interface

Block Diagram





Ordering Information



Military Version

The following table gives package/access time/process flow available combinations

Temp. range	Packages	The state of the s	Access	Time (ns)		Std process 6570%
		25 (H)	35 (K)	45 (M)	55 (N)	Mil flows (including SMD5962-88681)
М	1 4 0	• • X	• • X	• • X	1	:

= product in production

X = call sales office for availability